

# Ziyuan Lin

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11697302/publications.pdf>

Version: 2024-02-01

20  
papers

2,600  
citations

516215

16  
h-index

794141

19  
g-index

20  
all docs

20  
docs citations

20  
times ranked

4698  
citing authors

#	ARTICLE	IF	CITATIONS
1	Optoelectronic resistive random access memory for neuromorphic vision sensors. Nature Nanotechnology, 2019, 14, 776-782.	15.6	783
2	Extraordinarily Strong Interlayer Interaction in 2D Layered PtS <sub>2</sub> . Advanced Materials, 2016, 28, 2399-2407.	11.1	415
3	Fabrication of Nickel-Cobalt Bimetal Phosphide Nanocages for Enhanced Oxygen Evolution Catalysis. Advanced Functional Materials, 2018, 28, 1706008.	7.8	370
4	Direct TEM observations of growth mechanisms of two-dimensional MoS <sub>2</sub> flakes. Nature Communications, 2016, 7, 12206.	5.8	179
5	Carrier Type Control of WSe <sub>2</sub> Field-Effect Transistors by Thickness Modulation and MoO <sub>3</sub> Layer Doping. Advanced Functional Materials, 2016, 26, 4223-4230.	7.8	167
6	Controllable Growth of Large-Size Crystalline MoS <sub>2</sub> and Resist-Free Transfer Assisted with a Cu Thin Film. Scientific Reports, 2016, 5, 18596.	1.6	163
7	Low voltage and high ON/OFF ratio field-effect transistors based on CVD MoS <sub>2</sub> and ultra high-k gate dielectric PZT. Nanoscale, 2015, 7, 8695-8700.	2.8	121
8	Active site engineering of Fe- and Ni-sites for highly efficient electrochemical overall water splitting. Journal of Materials Chemistry A, 2018, 6, 21445-21451.	5.2	68
9	Two-Dimensional Antiferroelectricity in Nanostripe-Ordered $\ln_2\text{S}_3$ . Physical Review Letters, 2020, 125, 047601.	2.9	58
10	Low-Power Complementary Inverter with Negative Capacitance 2D Semiconductor Transistors. Advanced Functional Materials, 2020, 30, 2003859.	7.8	58
11	Improved interfacial H <sub>2</sub> O supply by surface hydroxyl groups for enhanced alkaline hydrogen evolution. Journal of Materials Chemistry A, 2017, 5, 24091-24097.	5.2	47
12	Phase and Facet Control of Molybdenum Carbide Nanosheet Observed by In Situ TEM. Small, 2017, 13, 1700051.	5.2	41
13	Emerging Group-VI Elemental 2D Materials: Preparations, Properties, and Device Applications. Small, 2020, 16, e2003319.	5.2	38
14	Doping of two-dimensional MoS <sub>2</sub> by high energy ion implantation. Semiconductor Science and Technology, 2017, 32, 124002.	1.0	26
15	Infrared light gated MoS <sub>2</sub> field effect transistor. Optics Express, 2015, 23, 31908.	1.7	18
16	Interstitial copper-doped edge contact for n-type carrier transport in black phosphorus. Information Materials, 2019, 1, 242-250.	8.5	18
17	Topological phase change transistors based on tellurium Weyl semiconductor. Science Advances, 2022, 8, .	4.7	17
18	Quasi one-dimensional van der Waals gold selenide with strong interchain interaction and giant magnetoresistance. Science Bulletin, 2020, 65, 1451-1459.	4.3	7

#	ARTICLE	IF	CITATIONS
19	Two-Dimensional Tellurene Transistors with Low Contact Resistance and Self-Aligned Catalytic Thinning Process. <i>Advanced Electronic Materials</i> , 2022, 8, .	2.6	5
20	Improved performance of HEMTs with BN as heat dissipation. , 2016, , .		1